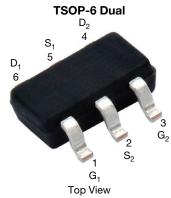
SQ3989EV

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Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



Marking Code: 9B

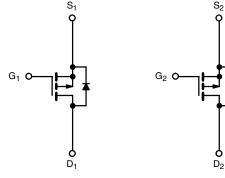
PRODUCT SUMMARY					
V _{DS} (V)	-30				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	-0.155				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 \text{ V}$	-0.300				
I _D (A)	-2.32				
Configuration	Dual				
Package	TSOP-6				

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (Γ _A = 25 °C, unless c	otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	-30	V	
Gate-source voltage	V _{GS}	± 20	v	
Continuous drain surront $(T_{-} = 150 \text{ °C})^{3}$	T _C = 25 °C	1	-2.5	
Continuous drain current (T _J = 150 °C) ^a	T _C = 125 °C		-1.5	•
Pulsed drain current	I _{DM}	-10.2	— A	
Continuous source current (diode conduction) ^a	I _S	-2.1		
Maximum power dissinction a	T _C = 25 °C	D	1.67	w
Maximum power dissipation ^a	T _C = 125 °C	P _D	0.56	V
Unclamped inductive surge UIS		I _{AV}	7	А
Operating junction and storage temperature range	ge	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Maximum junction-to-ambient ^a	Steady state	R _{thJA}	150	°C/W	
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	90	0/10	

Note

a. Surface mounted on 1" x 1" FR4 board

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SPECIFICATIONS ($T_J = 25^{\circ}C$, unless otherwise noted)								
PARAMETER	SYMBOL	Т	MIN.	TYP.	MAX.	UNIT		
Static								
Gate threshold voltage	V _{GS(th)}	V _{DS}	_S = V _{GS} , I _D = -250 μA	-0.6	-	-1.5	V	
Gate-body leakage	I _{GSS}	V _{DS}	$_{\rm S}$ = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
Zero gate voltage drain	lana	$V_{GS} = 0 V$	$V_{DS} = -30 V$	-	-	-1		
current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -30 V, T_J = 55 °C	-	-	-5	μA	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-4	-	-	А	
Drain-source on-state	R _{DS(on)}	$V_{GS} = -10 V$	I _D = -0.4 A	-	0.140	0.155	Ω	
resistance ^a		$V_{GS} = -4.5 V$	I _D = -0.2 A	-	0.265	0.300		
Forward transconductance ^a	9 _{fs}	$V_{DS} = -5 V, I_D = -1 A$		-	2.2	-	S	
Diode forward voltage ^a	V _{SD}	I _S = -0.5 A, V _{GS} = 0 V		-	-0.83	-1.1	V	
Dynamic ^b								
Total gate charge	Qg		V _{DS} = -15 V, I _D = -3 A	-	8.6	11.1		
Gate-source charge	Q _{gs}	$V_{GS} = -10 V$		-	1.2	-	nC	
Gate-drain charge	Q _{gd}			-	3	-		
Gate resistance	R _g	f = 1 MHz		2.5	-	7.2	Ω	
Turn-on delay time	t _{d(on)}			-	5.7	8		
Rise time	t _r	$V_{DD} = -10 \text{ V}, \text{ R}_L = 10 \ \Omega$ $\text{I}_D \cong -1 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_g = 1 \text{ k}\Omega$		-	3	4	ns	
Turn-off delay time	t _{d(off)}			-	13.8	18		
Fall time	t _f			-	2	3]	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

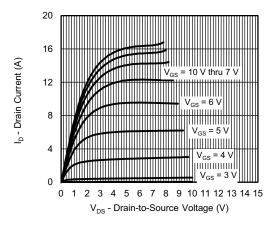
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



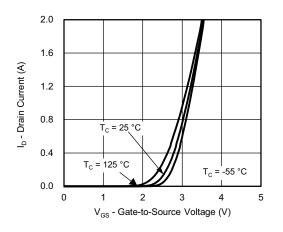
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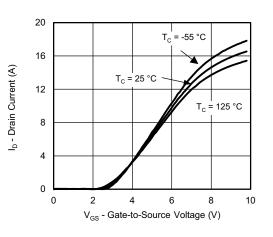
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



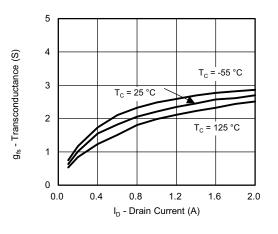
Output Characteristics



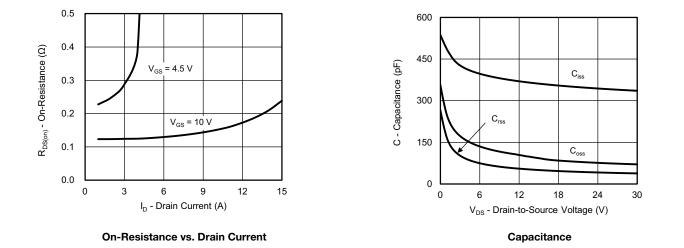
Transfer Characteristics



Transfer Characteristics



Transconductance



S17-1209-Rev. D, 26-Jul-17

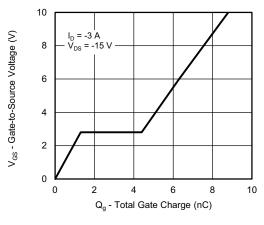
3 ions, contact: automostechsur Document Number: 75059

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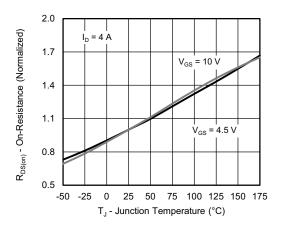


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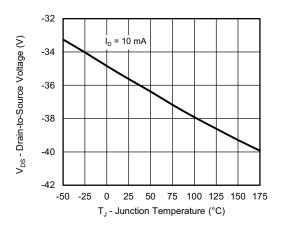
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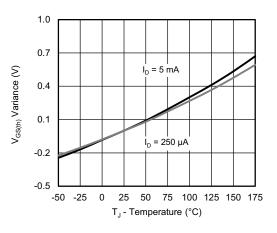
Gate Charge



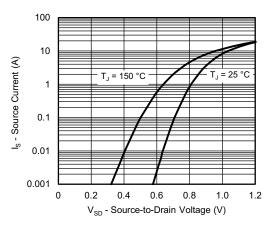
On-Resistance vs. Junction Temperature



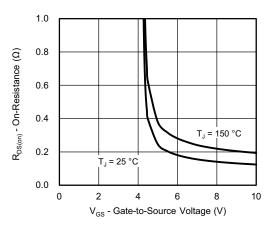
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

S17-1209-Rev. D, 26-Jul-17

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Document Number: 75059

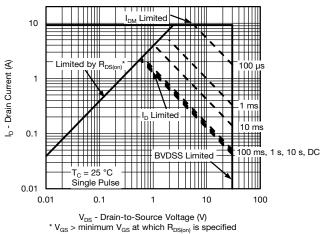
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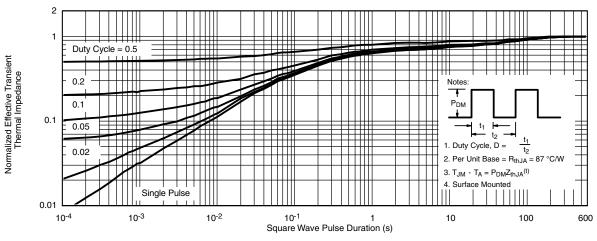
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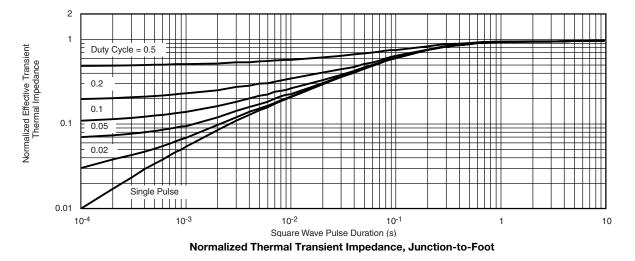
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



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Package Information

Vishay Siliconix

TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MILLIMETERS			I			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071 0.075 0		0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂	0.25 BSC				0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom				7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)

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